

**Amendments to the Claims:**

The claims in this listing will replace all prior claims in the application.

**Listing of Claims:**

1. (Currently Amended) A mask comprising:  
a mask substrate[[],]; and  
at least one annular equal line space phase shifting pattern on said mask substrate  
to produce ~~an opaque~~ a substantially unexposed region on a semiconductor  
substrate, ~~the at least one annular equal line space phase shifting pattern including:~~  
an annular ring, and  
a central portion, wherein a mask pitch of said at least one annular equal  
line space phase shifting pattern is smaller than two times of a  
corresponding critical dimension pitch on said semiconductor substrate.
2. (Canceled)
3. (Currently Amended) The mask of claim [[2]]1, wherein said annular ring  
has a phase shift of approximately 180 degrees from that of said mask substrate and said  
central portion.
4. (Currently Amended) The mask of claim 1, wherein said at least one annular  
equal line space phase shifting pattern further comprises a plurality of annular rings ~~and a~~  
~~central portion.~~
5. (Currently Amended) The mask of claim 4, wherein an outermost annular  
ring has a phase shift of approximately 180 degrees from that of said mask substrate and  
an adjacent inner annular ring, each inner annular ring having a phase shift of

approximately 180 degrees from that of its outer adjacent annular ring, and said central portion having a phase shift of approximately 180 degrees from that of an innermost ring.

6. (Original) The mask of claim 1, wherein said mask substrate comprises quartz.

7. (Currently Amended) The mask of claim 1, wherein said at least one annular equal line space phase shifting pattern is substantially transparent to an incident radiation for photomasking.

8. (Canceled)

9. (Currently Amended) A method of manufacturing a mask, comprising:  
providing a mask substrate;  
forming a layer of resist material over said mask substrate;  
patterning ~~at least one annular equal line space phase shifting pattern on~~ said resist layer;

patterning ~~[[said]]~~ at least one annular equal line space phase shifting pattern ~~[[onto]] on~~ said mask substrate, the at least one annular equal line space phase shifting pattern including an annular ring and a central portion, wherein a mask pitch of said at least one annular equal line space phase shifting pattern being smaller than two times of a corresponding critical dimension pitch on said semiconductor substrate; and

removing a remaining portion of said resist layer.

10. (Currently Amended) A method of manufacturing a mask, comprising:  
providing a mask substrate;  
forming a layer of conductive material over said mask substrate;  
forming a layer of resist material over said conductive layer;  
patterning ~~at least one annular equal line space phase shifting pattern on~~ said resist layer;

patterning ~~said pattern~~ onto said conductive layer;

removing a remaining portion of said resist layer;

patterning ~~said pattern~~ onto said mask substrate at least one annular equal line space phase shifting pattern including an annular ring and a central portion, wherein a mask pitch of said at least one annular equal line space phase shifting pattern being smaller than two times of a corresponding critical dimension pitch on said semiconductor substrate; and

removing a remaining portion of said conductive layer.

11. (Original) The method of claim 10, wherein said mask substrate comprises quartz.

12. (Original) The method of claim 10, wherein said layer of conductive material comprises chrome.

13. (Currently Amended) The method of claim 10, wherein said at least one annular equal line space phase shifting pattern comprises an annular ring and a central portion.

14. (Currently Amended) The method of claim 10, wherein said at least one annular equal line space phase shifting pattern comprises a plurality of annular rings and a central portion

15. (Currently Amended) The method of claim 10, wherein said at least one annular equal line space phase shifting pattern is formed on said mask substrate by etching said mask substrate.

16. (Original) The method of claim 10, wherein said pattern is formed on said mask substrate by disposing phase shifting material on said mask substrate.

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17-22. (Cancelled)